2SB1156

Silicon PNP epitaxial planar type

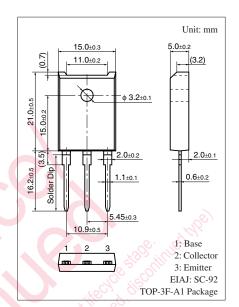
For power switching Complementary to 2SD1707

■ Features

- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Large collector current I_C
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit		
Collector-base voltage (Emit	V_{CBO}	-130	V		
Collector-emitter voltage (Ba	V_{CEO}	-80	V		
Emitter-base voltage (Collect	V_{EBO}	-7	V		
Collector current	I_{C}	-20	A		
Peak collector current	I _{CP}	-30	A		
Collector power dissipation		P _C	100	W	
T	a = 25°C		3		
Junction temperature	> . <(T_{j}	150	°C	
Storage temperature		T_{stg}	-55 to +150	°C	
				_	



■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

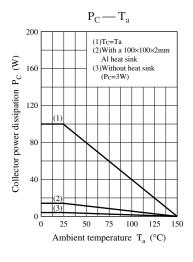
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -10 \text{ mA}, I_B = 0$	-80			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -100 \text{ V}, I_E = 0$			-10	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-50	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$	45			_
	h _{FE2} *	$V_{CE} = -2 \text{ V}, I_{C} = -3 \text{ A}$	60		260	
	h _{FE3}	$V_{CE} = -2 \text{ V}, I_{C} = -10 \text{ A}$	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	$I_C = -8 \text{ A}, I_B = -0.4 \text{ A}$			- 0.5	V
	V _{CE(sat)2}	$I_C = -20 \text{ A}, I_B = -2 \text{ A}$			-1.5	
Base-emitter saturation voltage	V _{BE(sat)1}	$I_C = -8 \text{ A}, I_B = -0.4 \text{ A}$			-1.5	V
	V _{BE(sat)2}	$I_C = -20 \text{ A}, I_B = -2 \text{ A}$			-2.5	
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time	t _{on}	$I_C = -8 \text{ A}, I_{B1} = -0.8 \text{ A}, I_{B2} = 0.8 \text{ A}$		0.5		μs
Storage time	t _{stg}	$V_{CC} = -50 \text{ V}$		1.0		μs
Fall time	t _f			0.2		μs

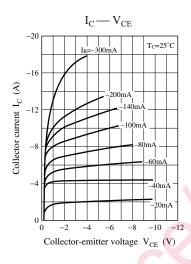
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

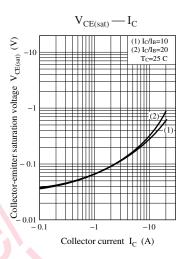
2. *: Rank classification

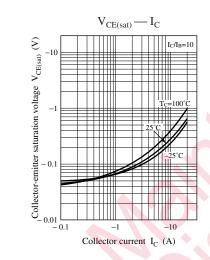
Rank	R	Q	Р
h _{FE2}	60 to 120	90 to 180	130 to 260

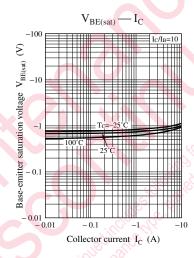
Ordering can be made by the common rank (PQ rank $h_{FE2} = 60$ to 240) in the rank classification.

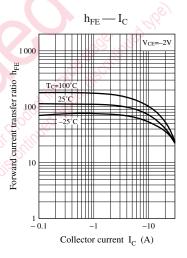


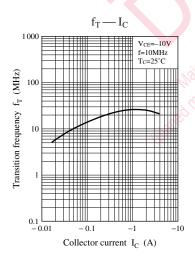


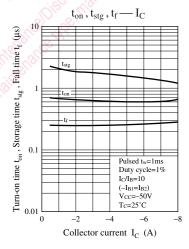


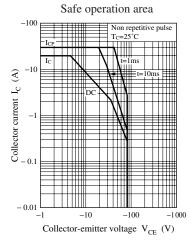


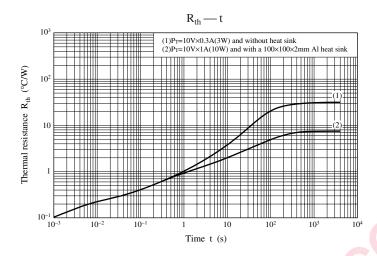












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